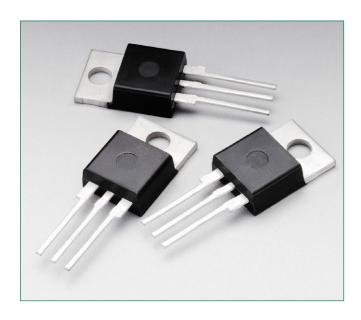


# MAC16DG, MAC16MG, MAC16NG





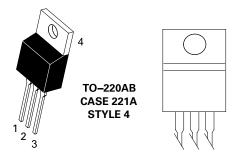
# **Description**

Designed for high performance full-wave ac control applications where high noise immunity and high commutating di/dt are required.

# **Features**

- Blocking Voltage to 800
- On-State Current Rating of 16 Amperes RMS at 80°C
- Uniform Gate Trigger Currents in Three Quadrants
- High Immunity to dv/ dt – 500 V/µs minimum at 125°C
- Minimizes Snubber Networks for Protection
- Industry Standard TO-220 Package
- High Commutating di/ dt – 9.0 A/ms minimum at 125°C
- These Devices are Pb-Free and are RoHS Compliant

# **Pin Out**



# **Functional Diagram**



# **Additional Information**



**Datasheet** 



Resources



Samples



# Maximum Ratings (T<sub>J</sub> = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit	
Peak Repetitive Off-State Voltage (Note 1) (- 40 to 125°C, Sine Wave, 50 to 60 Hz, Gate Open)	MAC16D MAC16M MAC16N	V <sub>DRM</sub> ,	400 600 800	V
On-State RMS Current (Full Cycle Sine Wave, 50 to 60 Hz, T <sub>C</sub> = 80°C)	I <sub>T (RMS)</sub>	16	А	
Peak Non-Repetitive Surge Current (One Full Cycle Sine Wave, 60 Hz, $T_c$ = 125°C)		I <sub>TSM</sub>	150	А
Circuit Fusing Consideration (t = 8.3 ms)	l²t	93	A <sup>2</sup> sec	
Peak Gate Power (T <sub>C</sub> = +80°C, Pulse Width = 1.0 µs)		P <sub>GM</sub>	20	W
Average Gate Power (t = 8.3 ms, T <sub>c</sub> = 80°C)		P <sub>G(AV)</sub>	0.5	W
Operating Junction Temperature Range		T <sub>J</sub>	-40 to +125	°C
Storage Temperature Range		T <sub>stg</sub>	-40 to +125	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied.

#### **Thermal Characteristics**

Rating		Symbol	Value	Unit
Thermal Resistance,	Junction-to-Case (AC) Junction-to-Ambient	R <sub>ejc</sub> R <sub>eja</sub>	2.0 62.5	°C/W
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 10 seconds		T <sub>L</sub>	260	°C

# Electrical Characteristics - OFF (T, = 25°C unless otherwise noted; Electricals apply in both directions)

Characteristic		Symbol	Min	Тур	Max	Unit
Peak Repetitive Blocking Current	T, = 25°C	I <sub>DRM</sub> ,	-	-	0.01	A
$(V_D = V_{DRM} = V_{RRM}, Gate Open)$	T <sub>J</sub> = 125°C	I <sub>RRM</sub>	-	-	2.0	mA

#### Electrical Characteristics - ON (T<sub>1</sub> = 25°C unless otherwise noted; Electricals apply in both directions)

Characteristic		Symbol	Min	Тур	Max	Unit	
Peak On–State Voltage (Note 2) ( $I_{TM} = \pm 21 \text{ A Peak}$ )		V <sub>TM</sub>	-	1.2	1.6	V	
Gate Trigger Current	MT2(+), G(+)		10	16	50		
(Continuous dc)	MT2(+), G(-)	l <sub>GT</sub>	10	18	50	mA	
$(V_D = 12 \text{ V}, R_L = 100 \Omega)$	MT2(-), G(-)		10	22	50		
Gate Trigger Voltage	MT2(+), G(+)	V <sub>GT</sub>	0.5	0.75	1.5		
(Continuous dc)	MT2(+), G(-)		V <sub>GT</sub>	0.5	0.72	1.5	V
$(V_{D} = 12 \text{ V}, \text{ R}_{L} = 100 \Omega)$	MT2(-), G(-)			0.5	0.82	1.5	
	MT2(+), G(+)		-	33	50		
Latching Current $(V_D = 24 \text{ V}, I_G = 35 \text{ mA})$	MT2(+), G(-)	V <sub>GD</sub>	-	36	80	V	
	MT2(-), G(-)		-	33	50		
Holding Current (V <sub>D</sub> = 12 V <sub>dc</sub> , Gate Open, Initiating Current = ±200 mA))		I <sub>H</sub>	-	20	50	mA	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions

2. Indicates Pulse Test: Pulse Width  $\leq$  2.0 ms, Duty Cycle  $\leq$  2%.

Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. V<sub>DRM</sub> and V<sub>RRM</sub> for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

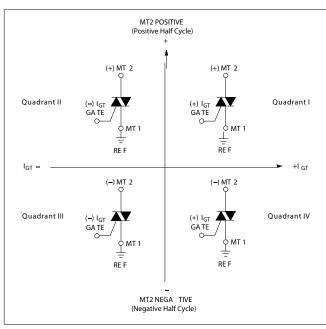


Dynamic Characteristics						
Characteristic	Symbol	Min	Тур	Max	Unit	
Rate of Change of Commutating Current, See Figure 10. (VD = $400 \text{ V}$ , ITM = $6.0 \text{ A}$ , Commutating dv/dt = $24 \text{ V/}\mu\text{s}$ , Gate Open, TJ = $125^{\circ}\text{C}$ , f = $250 \text{ Hz}$ , No Snubber)	(di/dt)c	9.0	_	_	A/ms	
Critical Rate of Rise of Off-State Voltage ( $V_D = Rated V_{DRM}$ , Exponential Waveform, Gate Open, $T_J = 125$ °C)	dv/dt	600	_	-	V/µs	

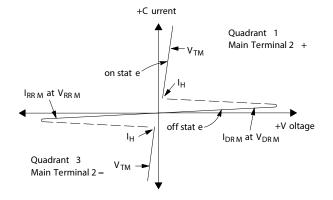
# **Voltage Current Characteristic of SCR**

Symbol	Parameter
V <sub>DRM</sub>	Peak Repetitive Forward Off State Voltage
IDRM	Peak Forward Blocking Current
V <sub>RRM</sub>	Peak Repetitive Reverse Off State Voltage
I <sub>RRM</sub>	Peak Reverse Blocking Current
V <sub>TM</sub>	Maximum On State Voltage
I <sub>H</sub>	Holding Current

# **Quadrant Definitions for a Triac**



All polarities are referenced to MT1.
With in–phase signals (using standard AC lines) quadrants I and III are used







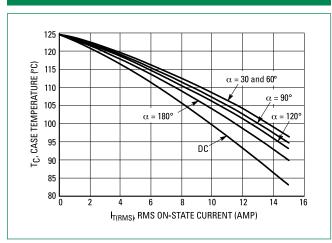


Figure 2. On-State Power Dissipation

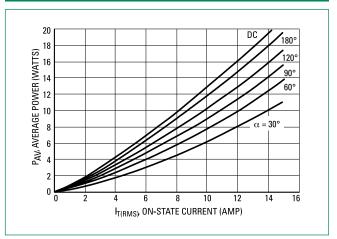


Figure 3. On-State Characteristics

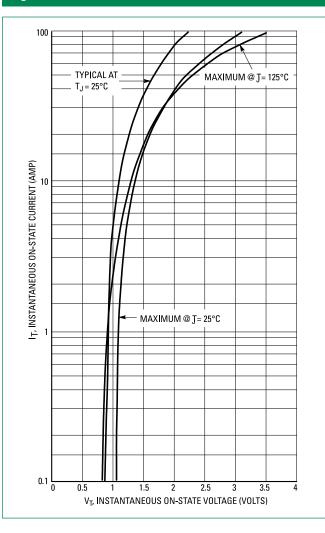


Figure 4. Thermal Response

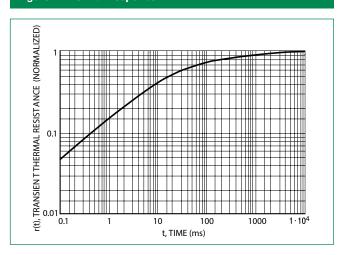


Figure 5. Hold Current Variation

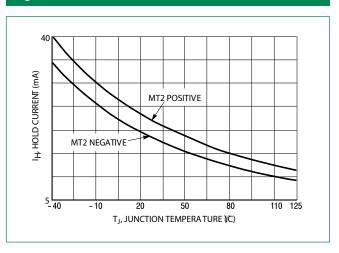




Figure 6. Typical Holding Current vs Junction Temperature

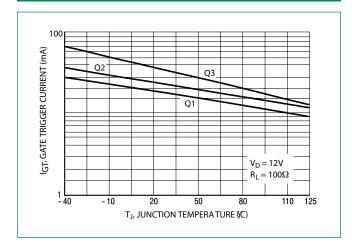


Figure 7. Gate Trigger Voltage vs Junction Temperature

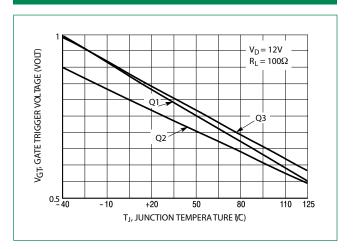


Figure 8. Critical Rate of Rise of Off–State Voltage (Exponential)

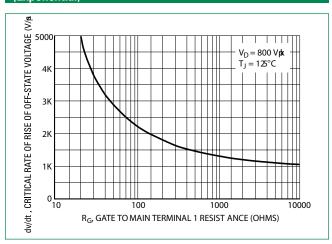


Figure 9. Critical Rate of Rise of Commutating Voltage

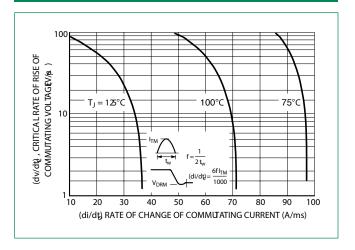
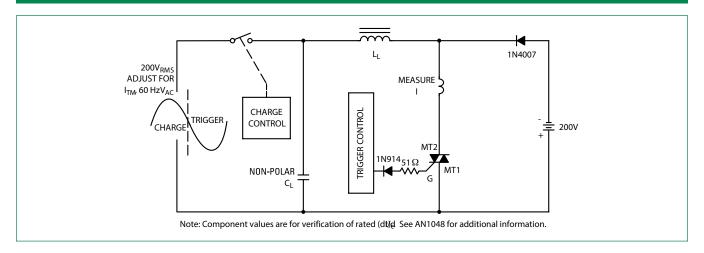
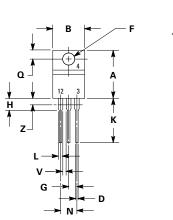


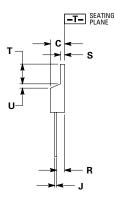
Figure 10. Simplified Test Circuit to Measure the Critical Rate of Rise of Commutating Current (di/dt)c



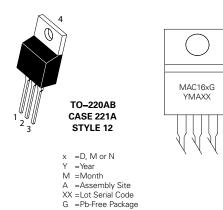


#### **Dimensions**





# **Part Marking System**



Dim	Inc	Inches		neters
Dim	Min	Max	Min	Max
Α	0.590	0.620	14.99	15.75
В	0.380	0.420	9.65	10.67
С	0.178	0.188	4.52	4.78
D	0.025	0.035	0.64	0.89
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.41	2.67
Н	0.110	0.130	2.79	3.30
J	0.018	0.024	0.46	0.61
K	0.540	0.575	13.72	14.61
L	0.060	0.075	1.52	1.91
N	0.195	0.205	4.95	5.21
Q	0.105	0.115	2.67	2.92
R	0.085	0.095	2.16	2.41
s	0.045	0.060	1.14	1.52
Т	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045		1.15	_
Z	_	0.080	_	2.04

Pin Assignment			
1	Main Terminal 1		
2	Main Terminal 2		
3	Gate		
4	No Connection		

Ordering Information					
Device	Package	Shipping			
MAC16DG					
MAC16MG	TO-220 (Pb-Free)	500 Units/ Rail			
MAC16NG	(1 2 1 1 0 0 )				

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH.
- DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.